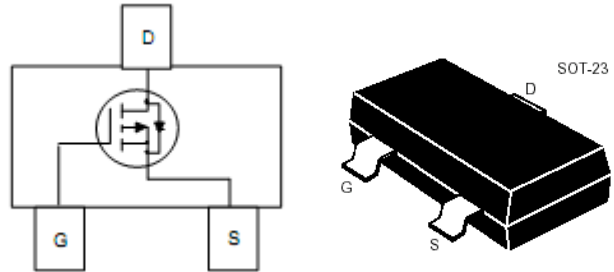




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SOT-23 場效應晶體管(SOT-23 Field Effect Transistors)



**P-Channel Enhancement-Mode MOS FETs**

**P 沟道增强型 MOS 场效应管**

**■MAXIMUM RATINGS 最大額定值**

Characteristic 特性參數	Symbol 符號	Max 最大值	Unit 單位
Drain-Source Voltage 漏極-源極電壓	$BV_{DSS}$	-20	V
Gate- Source Voltage 柵極-源極電壓	$V_{GS}$	$\pm 8$	V
Drain Current (continuous) 漏極電流-連續	$I_D$	-2.4	A
Drain Current (pulsed) 漏極電流-脉冲	$I_{DM}$	-10	A
Total Device Dissipation 總耗散功率 $T_A=25^{\circ}C$ 環境溫度為 $25^{\circ}C$	$P_D$	900	mW
Junction 結溫	$T_J$	150	$^{\circ}C$
Storage Temperature 儲存溫度	$T_{stg}$	-55to+150	$^{\circ}C$

**■DEVICE MARKING 打標**

**GM2015=WT1**



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**ELECTRICAL CHARACTERISTICS 電特性**

( $T_A=25^{\circ}\text{C}$  unless otherwise noted 如無特殊說明，溫度為  $25^{\circ}\text{C}$ )

Characteristic 特性參數	Symbol 符號	Min 最小值	Typ 典型值	Max 最大值	Unit 單位
Drain-Source Breakdown Voltage 漏極-源極擊穿電壓( $I_D = -250\mu\text{A}, V_{GS}=0\text{V}$ )	$BV_{DSS}$	-20	—	—	V
Gate Threshold Voltage 柵極開啓電壓( $I_D = -250\mu\text{A}, V_{GS}=V_{DS}$ )	$V_{GS(th)}$	-0.4	—	-1	V
Drain-Source On Voltage 漏極-源極導通電壓( $I_D = -50\text{mA}, V_{GS} = -5\text{V}$ ) ( $I_D = -500\text{mA}, V_{GS} = -10\text{V}$ )	$V_{DS(ON)}$	—	—	-0.375 -3.75	V
Diode Forward Voltage Drop 內附二極管正向壓降( $I_S = -0.75\text{A}, V_{GS}=0\text{V}$ )	$V_{SD}$	—	—	-1.2	V
Zero Gate Voltage Drain Current 零柵壓漏極電流( $V_{GS}=0\text{V}, V_{DS} = -16\text{V}$ ) ( $V_{GS}=0\text{V}, V_{DS} = -16\text{V}, T_A=55^{\circ}\text{C}$ )	$I_{DSS}$	—	—	-1 -10	$\mu\text{A}$
Gate Body Leakage 柵極漏電流( $V_{GS}=\pm 8\text{V}, V_{DS}=0\text{V}$ )	$I_{GSS}$	—	—	$\pm 100$	nA
Static Drain-Source On-State Resistance 靜態漏源導通電阻( $I_D = -2.7\text{A}, V_{GS} = -4.5\text{V}$ ) ( $I_D = -2.2\text{A}, V_{GS} = -2.5\text{V}$ )	$R_{DS(ON)}$	—	—	110 150	$\text{m}\Omega$
Input Capacitance 輸入電容 ( $V_{GS}=0\text{V}, V_{DS} = -6\text{V}, f=1\text{MHz}$ )	$C_{ISS}$	—	—	880	pF
Common Source Output Capacitance 共源輸出電容( $V_{GS}=0\text{V}, V_{DS} = -6\text{V}, f=1\text{MHz}$ )	$C_{OSS}$	—	—	270	pF
Turn-ON Time 開啓時間 ( $V_{DS} = -6\text{V}, I_D = -1\text{A}, R_{GEN}=6\Omega$ )	$t_{(on)}$	—	—	20	ns
Turn-OFF Time 關斷時間 ( $V_{DS} = -6\text{V}, I_D = -1\text{A}, R_{GEN}=6\Omega$ )	$t_{(off)}$	—	—	65	ns

Pulse Width $\leq 300\mu\text{s}$ ; Duty Cycle $\leq 2.0\%$



**宇芯微**  
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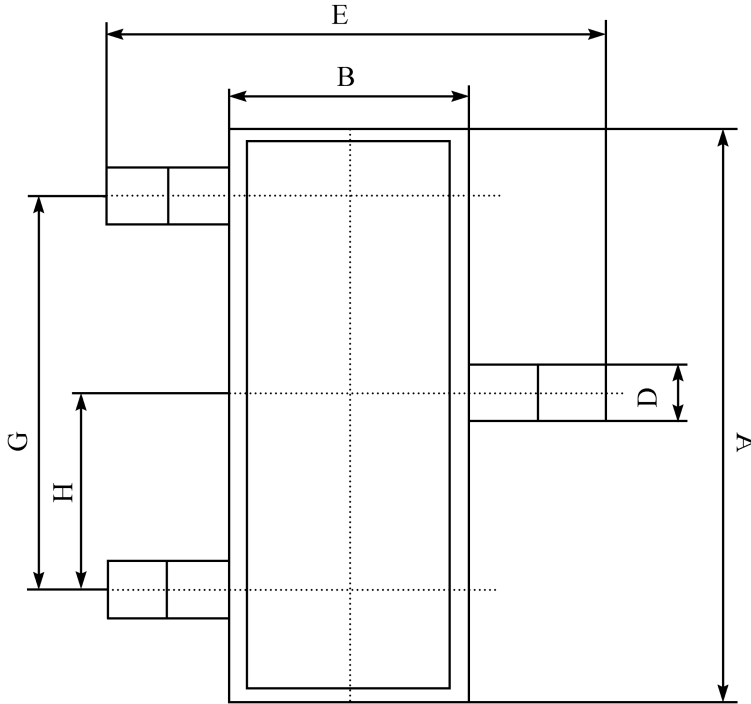
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■DIMENSION 外形封装尺寸

單位(UNIT): mm



序號	數值及公差
A	2.90±0.10
B	1.30±0.10
C	1.00±0.10
D	0.40±0.10
E	2.40±0.20
G	1.90±0.10
H	0.95±0.05
J	0.13±0.05
K	0.00-0.10
M	≥0.2
N	0.60±0.10
P	7±2°

